











Software

SCDS337D - DECEMBER 2012-REVISED NOVEMBER 2017

**TS3USB3000** 

# TS3USB3000 DPDT USB 2.0 High-Speed and Mobile High-Definition Link (MHL) 6.1-GHz Switch

#### **Features**

V<sub>CC</sub> Range 2.3 V to 4.8 V

Mobile Hi-Definition Link (MHL) Switch:

Bandwidth (–3 dB): 6.1 GHz

R<sub>ON</sub> (Typical): 5.7 Ω

- C<sub>ON</sub> (Typical): 1.6 pF

**USB Switch:** 

- Bandwidth (-3 dB): 6.1 GHz

R<sub>ON</sub> (Typical): 4.6 Ω

C<sub>ON</sub> (Typical): 1.4 pF

Current Consumption: 30 µA (Typical)

Special Features:

I<sub>OFF</sub> Protection Prevents Current Leakage in Powered-Down State ( $V_{CC}$  and  $V_{BUS} = 0 \text{ V}$ )

1.8-V Compatible Control Inputs (SEL, OE)

 Overvoltage Tolerance (OVT) on all I/O Pins up to 5.5 V Without External Components

Overvoltage Protection When 9-V Short to D-Pin

**ESD Performance:** 

3.5-kV Human Body Model (A114B, Class II)

1-kV Charged-Device Model (C101)

10-Pin UQFN Package (1.5-mm × 2-mm, 0.5-mm Pitch)

# **Applications**

- Smartphones, Tablets, Mobile
- Portable Instrumentation
- Digital Still Cameras

# 3 Description

The TS3USB3000 device is a double-pole, double throw (DPDT) multiplexer that includes a high-speed Mobile High-Definition Link (MHL) switch and an USB 2.0 High-Speed (480 Mbps) switch in the same package. These configurations allow the system designer to use a common USB or Micro-USB connector for both MHL video signals and USB data.

The TS3USB3000 has a  $V_{CC}$  range of 2.3 V to 4.8 V and supports overvoltage tolerance (OVT) feature, which allows the I/O pins to withstand overvoltage conditions (up to 5.5 V). The power-off protection feature forces all I/O pins to be in high-impedance mode when power is not present, allowing full isolation of the signal lines under such condition without excessive leakage current. The select pins of TS3USB3000 are compatible with 1.8-V control voltage, allowing them to be directly interfaced with the General-Purpose I/O (GPIO) from a mobile processor.

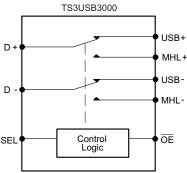
The TS3USB3000 comes with a small 10-pin UQFN package with only 1.5 mm × 2 mm in size, which makes it a perfect candidate to be used in mobile applications.

# Device Information (1)

PART NUMBER	PACKAGE	BODY SIZE (NOM)
TS3USB3000	UQFN (10)	1.50 mm × 2.00 mm

(1) For all available packages, see the orderable addendum at the end of the data sheet.

#### **Functional Block Diagram**



Copyright © 2017. Texas Instruments Incorporated

Features ...... 1

Page



Т	'n	h	۵۱	of	F (	```	'n	ite	n	tc
	a	v		v			,,,	ııc		LZ

0.1 Application Information 10	2	Applications 1		8.4 Device Functional Modes	12
4 Revision History. 2 9.1 Application Information 13 5 Pin Configuration and Functions 3 9.2 Typical Application 13 6 Specifications. 4 10 Power Supply Recommendations 17 6.1 Absolute Maximum Ratings 4 11 Layout 17 6.2 ESD Ratings 4 11.1 Layout Guidelines 17 6.3 Recommended Operating Conditions 4 11.1 Layout Example 18 6.4 Thermal Information 5 12 Device and Documentation Support 19 6.5 Electrical Characteristics 5 12.1 Documentation Support 19 6.6 Dynamic Characteristics 6 12.2 Receiving Notification of Documentation Updates 19 6.6 Dynamic Characteristics 6 12.3 Community Resources 19 6.8 Typical Characteristics 7 12.4 Trademarks 19 7 Parameter Measurement Information 9 12.5 Electrostatic Discharge Caution 19 8 Detailed Description 10 10 8.1 Overview 10 11.2 Giossary 19 8.2 Functional Block Diagram 10 11.3 Mechanical, Packaging, and Orderable Information 19 8.2 Functional Block Diagram 10 13 Mechanical, Packaging, and Orderable Information 20  Revision History  Revision B (October 2015) to Revision D Page  Extended the IC recommended V <sub>CC</sub> operating range to V <sub>CC</sub> = 2.3 to 4.8 V in the Features, Description, Absolute Maximum Ratings, Recommended Operating Conditions, Electrical Characteristics, Dynamic Characteristics and Timing Requirements sections 5  Ranges from Revision A (April 2013) to Revision B Page  Added Pin Configuration and Functions section, ESD Ratings table, Feature Description section, Device Functional Modes, Application and Implementation section, Power Supply Recommendations section, Leyout section, Device	3	Description 1	9	Application and Implementation	13
5 Pin Configuration and Functions 3 9.2 Typical Application 13 6 Specifications. 4 10 Power Supply Recommendations 17 6.1 Absolute Maximum Ratings 4 11 Layout 17 6.2 ESD Ratings. 4 11.1 Layout Guidelines 17 6.3 Recommended Operating Conditions. 4 11.2 Layout Example 188 6.4 Thermal Information 5 12 Device and Documentation Support 19 6.5 Electrical Characteristics 5 12.2 Receiving Notification of Documentation Updates 19 6.6 Dynamic Characteristics 6 12.3 Community Resources 19 6.8 Typical Characteristics 7 12.4 Trademarks 19 7 Parameter Measurement Information 9 12.5 Electrosatic Discharge Caution 19 8.1 Overview 10 8.2 Functional Block Diagram 10 12.6 Glossary 19 8.2 Functional Block Diagram 10 13.1 Package Option Addendum Device Marking column 19 8.2 Function B (October 2015) to Revision D Page  Changed the Package Option Addendum Device Marking column 19 8.1 Added Pin Configuration and Functions section, ESD Ratings table, Feature Description section, Device Functional Modes, Application and Implementation section, Power Supply Recommendations section, Layout section, Device	4			9.1 Application Information	13
6 Specifications	5			9.2 Typical Application	13
6.1 Absolute Maximum Ratings 4 11 Layout	-		10	Power Supply Recommendations	17
6.2 ESD Ratings	٠	•	11	Layout	17
6.3 Recommended Operating Conditions 4 6.4 Thermal Information 5 6.5 Electrical Characteristics 5 6.6 Dynamic Characteristics 6 6.7 Timing Requirements 6 6.8 Typical Characteristics 7 7 12.4 Trademarks 19 8 Detailed Description 9 8 Detailed Description 10 8.1 Overview 10 8.2 Functional Block Diagram 10  Revision History  Tanges from Revision C (January 2017) to Revision D  Revision B (October 2015) to Revision C  Extended the IC recommended V <sub>CC</sub> operating range to V <sub>CC</sub> = 2.3 to 4.8 V in the Features, Description, Absolute Maximum Ratings, Recommended Operating Conditions, Electrical Characteristics, Dynamic Characteristics and Timing Requirements section, Device Functional Modes, Application and Implementation section, Power Supply Recommendations section, Layout section, Device Functional Modes, Application and Implementation section, Power Supply Recommendations section, Layout section, Device				11.1 Layout Guidelines	17
6.4 Thermal Information 5 Electrical Characteristics 5 12.1 Documentation Support 19 6.5 Electrical Characteristics 5 12.1 Documentation Support 19 6.6 Dynamic Characteristics 6 12.2 Receiving Notification of Documentation Updates 19 6.7 Timing Requirements 6 12.3 Community Resources 19 6.8 Typical Characteristics 7 12.4 Trademarks 19 6.8 Typical Characteristics 7 12.4 Trademarks 19 7 Parameter Measurement Information 9 12.5 Electrostatic Discharge Caution 19 12.6 Glossary 19 12.6 Glossary 19 12.6 Glossary 19 19 13 Mechanical, Packaging, and Orderable Information 19 13 Mechanical, Packaging, and Orderable Information 19 13.1 Package Option Addendum 20 14 15 Package Option Addendum 20 15 Page		•		11.2 Layout Example	18
6.5 Electrical Characteristics 5 12.1 Documentation Support 19 6.6 Dynamic Characteristics 6 12.2 Receiving Notification of Documentation Updates 19 6.7 Timing Requirements 6 12.3 Community Resources 19 6.8 Typical Characteristics 7 12.4 Trademarks 19 7 Parameter Measurement Information 9 12.5 Electrostatic Discharge Caution 19 8 Detailed Description 10 12.6 Glossary 19 8.1 Overview 10 13 Mechanical, Packaging, and Orderable Information 19 8.2 Functional Block Diagram 10 13.1 Package Option Addendum 19 14.6 Page  Changed the Package Option Addendum Device Marking column 19 15 Page  Extended the IC recommended V <sub>CC</sub> operating range to V <sub>CC</sub> = 2.3 to 4.8 V in the Features, Description, Absolute 19 16 Maximum Ratings, Recommended Operating Conditions, Electrical Characteristics, Dynamic Characteristics and 19 17 Timing Requirements sections 5  18 Page  Added Pin Configuration and Functions section, ESD Ratings table, Feature Description section, Device Functional 19 18 Mechanical Subject Conditions Section, Power Supply Recommendations section, Layout section, Device			12	Device and Documentation Support	19
6.6 Dynamic Characteristics 6 12.2 Receiving Notification of Documentation Updates 19 6.7 Timing Requirements 6 12.3 Community Resources 19 6.8 Typical Characteristics 7 12.4 Trademarks 19 7 Parameter Measurement Information 9 12.5 Electrostatic Discharge Caution 19 12.6 Glossary 19 19 13.1 Package Option Addendum 19 19 19 19 19 19 19 19 19 19 19 19 19					
6.7 Tíming Requirements				12.2 Receiving Notification of Documentation Upda	tes 19
6.8 Typical Characteristics		•		12.3 Community Resources	19
7 Parameter Measurement Information 9 12.5 Electrostatic Discharge Caution 19 8 Detailed Description 10 12.6 Glossary 19 8.1 Overview 10 13 Mechanical, Packaging, and Orderable Information 19 8.2 Functional Block Diagram 10 13.1 Package Option Addendum 19 13.1 Package Option Addendum 20  Revision History  Tanges from Revision C (January 2017) to Revision D Page  Changed the Package Option Addendum Device Marking column 19  Tanges from Revision B (October 2015) to Revision C Page  Extended the IC recommended V <sub>CC</sub> operating range to V <sub>CC</sub> = 2.3 to 4.8 V in the Features, Description, Absolute Maximum Ratings, Recommended Operating Conditions, Electrical Characteristics, Dynamic Characteristics and Timing Requirements sections 5  Tanges from Revision A (April 2013) to Revision B Page  Added Pin Configuration and Functions section, ESD Ratings table, Feature Description section, Device Functional Modes, Application and Implementation section, Power Supply Recommendations section, Layout section, Device				12.4 Trademarks	19
8 Detailed Description	7	• •		12.5 Electrostatic Discharge Caution	19
8.1 Overview 10 8.2 Functional Block Diagram 10 13 Mechanical, Packaging, and Orderable Information 19 13.1 Package Option Addendum 20  Revision History  Tanges from Revision C (January 2017) to Revision D Page  Changed the Package Option Addendum Device Marking column 19  Tanges from Revision B (October 2015) to Revision C Page  Extended the IC recommended V <sub>CC</sub> operating range to V <sub>CC</sub> = 2.3 to 4.8 V in the Features, Description, Absolute Maximum Ratings, Recommended Operating Conditions, Electrical Characteristics, Dynamic Characteristics and Timing Requirements sections 5  Tanges from Revision A (April 2013) to Revision B Page  Added Pin Configuration and Functions section, ESD Ratings table, Feature Description section, Device Functional Modes, Application and Implementation section, Power Supply Recommendations section, Layout section, Device					
Revision History  langes from Revision C (January 2017) to Revision D  Changed the Package Option Addendum Device Marking column  19  Extended the IC recommended V <sub>CC</sub> operating range to V <sub>CC</sub> = 2.3 to 4.8 V in the Features, Description, Absolute Maximum Ratings, Recommended Operating Conditions, Electrical Characteristics, Dynamic Characteristics and Timing Requirements sections  5  Enanges from Revision A (April 2013) to Revision B  Page  Added Pin Configuration and Functions section, ESD Ratings table, Feature Description section, Device Functional Modes, Application and Implementation section, Power Supply Recommendations section, Layout section, Device	Ü	8.1 Overview 10	13		19
Revision History  langes from Revision C (January 2017) to Revision D  Changed the Package Option Addendum Device Marking column  19  langes from Revision B (October 2015) to Revision C  Extended the IC recommended V <sub>CC</sub> operating range to V <sub>CC</sub> = 2.3 to 4.8 V in the Features, Description, Absolute  Maximum Ratings, Recommended Operating Conditions, Electrical Characteristics, Dynamic Characteristics and  Timing Requirements sections  5  langes from Revision A (April 2013) to Revision B  Page  Added Pin Configuration and Functions section, ESD Ratings table, Feature Description section, Device Functional  Modes, Application and Implementation section, Power Supply Recommendations section, Layout section, Device		8.2 Functional Block Diagram 10			
Extended the IC recommended $V_{CC}$ operating range to $V_{CC} = 2.3$ to $4.8$ V in the Features, Description, Absolute Maximum Ratings, Recommended Operating Conditions, Electrical Characteristics, Dynamic Characteristics and Timing Requirements sections	nar	ges from Revision C (January 2017) to Revision D			Page
Extended the IC recommended $V_{CC}$ operating range to $V_{CC}$ = 2.3 to 4.8 V in the <i>Features, Description, Absolute Maximum Ratings, Recommended Operating Conditions, Electrical Characteristics, Dynamic Characteristics</i> and <i>Timing Requirements</i> sections	С	hanged the <i>Package Option Addendum</i> Device Marking col	umn		19
Maximum Ratings, Recommended Operating Conditions, Electrical Characteristics, Dynamic Characteristics and Timing Requirements sections	nan	ges from Revision B (October 2015) to Revision C			Page
Added Pin Configuration and Functions section, ESD Ratings table, Feature Description section, Device Functional Modes, Application and Implementation section, Power Supply Recommendations section, Layout section, Device					
Added Pin Configuration and Functions section, ESD Ratings table, Feature Description section, Device Functional Modes, Application and Implementation section, Power Supply Recommendations section, Layout section, Device	N	laximum Ratings, Recommended Operating Conditions, Ele	ectrical (	Characteristics, Dynamic Characteristics and	5
Modes, Application and Implementation section, Power Supply Recommendations section, Layout section, Device	N	laximum Ratings, Recommended Operating Conditions, Ele	ectrical (	Characteristics, Dynamic Characteristics and	5
	<i>N T</i>	flaximum Ratings, Recommended Operating Conditions, Ele iming Requirements sections	ectrical (	Characteristics, Dynamic Characteristics and	
	nan A	Maximum Ratings, Recommended Operating Conditions, Electiming Requirements sections  Ages from Revision A (April 2013) to Revision B  Added Pin Configuration and Functions section, ESD Ratings  Modes, Application and Implementation section, Power Supp	s table,	Characteristics, Dynamic Characteristics and  Feature Description section, Device Functional ommendations section, Layout section, Device	Page

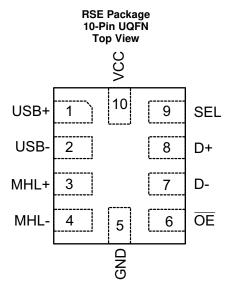
Submit Documentation Feedback

Changes from Original (December 2012) to Revision A

Copyright © 2012–2017, Texas Instruments Incorporated



# 5 Pin Configuration and Functions



# **Pin Functions**

F	PIN		PIN I/O		DESCRIPTION
NO.	NAME	1/0	DESCRIPTION		
1	USB+	I/O	USB data (Differential +)		
2	USB-	I/O	USB data (Differential –)		
3	MHL+	I/O	MHL data (Differential +)		
4	MHL-	I/O	MHL data (Differential –)		
5	GND	_	Ground		
6	ŌĒ	I	Output enable (Active low)		
7	D-	I/O	Data switch output (Differential –)		
8	D+	I/O	Data switch output (Differential +)		
9	SEL	I	Switch select (logic Low = D+/D- to USB+/USB- Logic High = D+/D- to MHL+/MHL-)		
10	VCC	_	Supply voltage		

Copyright © 2012–2017, Texas Instruments Incorporated



# 6 Specifications

#### 6.1 Absolute Maximum Ratings

over operating free-air temperature range (unless otherwise noted) (1) (2)

				MIN	MAX	UNIT
V <sub>CC</sub>	Supply voltage <sup>(3)</sup>			-0.3	5.5	V
$V_{I/O}$	Input-output DC voltage (3)			-0.3	5.5	V
$V_{D-}$	D- DC voltage <sup>(4)</sup>			-0.3	9	V
$V_{I}$	Digital input voltage (SEL, $\overline{\text{OE}}$ )			-0.3	5.5	V
I <sub>K</sub>	Input-output port diode current	VI/O < 0		<b>–</b> 50		mA
I <sub>IK</sub>	Digital logic input clamp current (3)	VI < 0		<b>-</b> 50		mA
I <sub>CC</sub>	Continuous current through VCC				100	mA
$I_{GND}$	Continuous current through GND			-100		mA
T <sub>stg</sub>	Storage temperature			<del>-</del> 65	150	°C

<sup>(1)</sup> Stresses beyond those listed under Absolute Maximum Ratings may cause permanent damage to the device. These are stress ratings only, which do not imply functional operation of the device at these or any other conditions beyond those indicated under Recommended Operating Conditions. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

(2) The algebraic convention, whereby the most negative value is a minimum and the most positive value is a maximum.

(3) All voltages are with respect to ground, unless otherwise specified.

# 6.2 ESD Ratings

			VALUE	UNIT
	, Electrostatic	Human body model (HBM), per ANSI/ESDA/JEDEC JS-001 (1)	±3500	V
V	(ESD) discharge	Charged-device model (CDM), per JEDEC specification JESD22-C101 (2)	±1000	V

<sup>(1)</sup> JEDEC document JEP155 states that 500-V HBM allows safe manufacturing with a standard ESD control process.

# 6.3 Recommended Operating Conditions

		MIN	MAX	UNIT
V <sub>CC</sub>	Supply voltage	2.3	4.8	V
V <sub>I/O (USB)</sub>	Analog voltage	0	3.6	V
V <sub>I/O</sub> (MHL)	Thatog Totago	•	0.0	
VI	Digital input voltage (SEL, OE)	0	$V_{CC}$	V
$T_{RAMP}(V_{CC})$	Power supply ramp time requirement (V <sub>CC</sub> )	100	1000	μs/V
T <sub>A</sub>	Operating free-air temperature	-40	85	ōC

Product Folder Links: TS3USB3000

<sup>(4)</sup> This rating only applies to the D- pin with respect to GND. VCC must be powered within the recommended operating conditions of 2.3 V to 4.8 V and the OE pin must be logic high for this rating to be applicable. Any condition where VCC is unpowered or the OE pin is not high must reference the rest of the *Absolute Maximum Ratings* Table.

<sup>(2)</sup> JEDEC document JEP157 states that 250-V CDM allows safe manufacturing with a standard ESD control process.



#### 6.4 Thermal Information

		TS3USB3000	
	THERMAL METRIC (1)	RSE (UQFN)	UNIT
		10 PINS	
$R_{\theta JA}$	Junction-to-ambient thermal resistance	191.6	°C/W
$R_{\theta JC(top)}$	Junction-to-case (top) thermal resistance	94.3	°C/W
$R_{\theta JB}$	Junction-to-board thermal resistance	117.5	°C/W
ΨЈТ	Junction-to-top characterization parameter	7.4	°C/W
ΨЈВ	Junction-to-board characterization parameter	117.4	°C/W

<sup>(1)</sup> For more information about traditional and new thermal metrics, see the Semiconductor and IC Package Thermal Metrics application report.

# 6.5 Electrical Characteristics

 $T_A = -40$ °C to +85°C, Typical values are at  $V_{CC} = 3.3$  V,  $T_A = 25$ °C, (unless otherwise noted)

1 <sub>A</sub> = -4		aiues aie al v <sub>CC</sub> = 3.0	3 V, I <sub>A</sub> = 25°C, (unless otherwise noted)				
	PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
MHL S	WITCH						
B	ON-state resistance	$V_{CC} = 2.7 \text{ V}$	$V_{I/O} = 1.65 \text{ V}, I_{ON} = -8 \text{ mA}$		5.7	9	Ω
R <sub>ON</sub>	ON-State resistance	V <sub>CC</sub> = 2.3 V	$V_{I/O} = 1.65 \text{ V}, I_{ON} = -8 \text{ mA}$		5.7	9.5	32
ΔR <sub>ON</sub>	ON-state resistance match between + and – paths	V <sub>CC</sub> = 2.3 V	$V_{I/O} = 1.65 \text{ V}, I_{ON} = -8 \text{ mA}$		0.1		Ω
R <sub>ON</sub> (FLAT)	ON-state resistance flatness	V <sub>CC</sub> = 2.3 V	$V_{I/O} = 1.65 \text{ V to } 3.45 \text{ V}, I_{ON} = -8 \text{ mA}$		1		Ω
l <sub>OZ</sub>	OFF leakage current	V <sub>CC</sub> = 4.8 V	Switch OFF, $V_{MHL\pm} = 1.65 \text{ V}$ to 3.45 V, $V_{D\pm} = 0 \text{ V}$	-2		2	μΑ
I <sub>OFF</sub>	Power-off leakage current	V <sub>CC</sub> = 0 V	Switch ON or OFF, $V_{MHL\pm}$ = 1.65 V to 3.45 V, $V_{D\pm}$ = NC	-10		10	μΑ
		V <sub>CC</sub> = 4.8 V	Switch ON, $V_{MHL\pm}$ = 1.65 V to 3.45 V, $V_{D\pm}$ = NC	-2		2	
I <sub>ON</sub> ON leakage current		V <sub>CC</sub> = 2.3 V	Switch ON, $V_{MHL\pm}$ = 1.65 V to 3.45 V, $V_{D\pm}$ = NC	-125		125	μΑ
USB S\	WITCH					•	
R <sub>ON</sub>	ON-state resistance	V <sub>CC</sub> = 2.3 V	$V_{I/O} = 0.4 \text{ V}, I_{ON} = -8 \text{ mA}$		4.6	7.5	Ω
ΔR <sub>ON</sub>	ON-state resistance match between + and – paths	V <sub>CC</sub> = 2.3 V	$V_{I/O} = 0.4 \text{ V}, I_{ON} = -8 \text{ mA}$		0.1		Ω
R <sub>ON</sub>	ON-state resistance flatness	V <sub>CC</sub> = 2.3 V	$V_{I/O} = 0 \text{ V to } 0.4 \text{ V}, I_{ON} = -8 \text{ mA}$		1		Ω
loz	OFF leakage current	V <sub>CC</sub> = 4.8 V	Switch OFF, $V_{USB\pm} = 0 \text{ V}$ to 3.6 V, $V_{D\pm} = 0 \text{ V}$	-2		2	μΑ
I <sub>OFF</sub>	Power-off leakage current	V <sub>CC</sub> = 0 V	Switch ON or OFF, $V_{USB\pm} = 0 \text{ V}$ to 3.6 V, $V_{D\pm} = \text{NC}$	-10		10	μΑ
	ON I a de la companie	V <sub>CC</sub> = 4.8 V	Switch ON, $V_{USB\pm} = 0$ V to 3.6 V, $V_{D\pm} = NC$	-2		2	
I <sub>ON</sub>	ON leakage current	V <sub>CC</sub> = 2.3 V	Switch ON, $V_{USB\pm} = 0$ V to 3.6 V, $V_{D\pm} = NC$	-125		125	μΑ
DIGITA	L CONTROL INPUTS (SE	L, <del>OE</del> )				<u></u>	
V <sub>IH</sub>	Input logic high	$V_{CC} = 2.3 \text{ V to } 4.8 \text{ V}$		1.3			٧
V <sub>IL</sub>	Input logic low	$V_{CC} = 2.3 \text{ V to } 4.8 \text{ V}$				0.6	٧
I <sub>IN</sub>	Input leakage current	$V_{CC} = 4.8 \text{ V}, V_{I/O} = 0 \text{ V}$	/ to 3.6 V, V <sub>IN</sub> = 0 to 4.8 V	-10		10	μΑ

Copyright © 2012–2017, Texas Instruments Incorporated



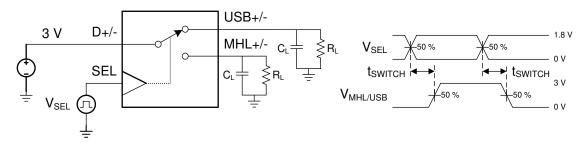
# 6.6 Dynamic Characteristics

over operating free-air temperature range (unless otherwise noted)

PARAMETER		TEST CONDITION	TEST CONDITIONS			MAX	UNIT
C <sub>ON(MHL)</sub>	MHL path ON capacitance	$V_{CC} = 3.3 \text{ V}, V_{I/O} = 0 \text{ or } 3.3 \text{ V},$ f = 240 MHz	Switch ON		1.6	2	pF
C <sub>ON(USB)</sub>	USB path ON capacitance	$V_{CC} = 3.3 \text{ V}, V_{I/O} = 0 \text{ or } 3.3 \text{ V},$ f = 240 MHz	Switch ON		1.4	2	pF
C <sub>OFF(MHL)</sub>	MHL path OFF capacitance	$V_{CC} = 3.3 \text{ V}, V_{I/O} = 0 \text{ or } 3.3 \text{ V}$ f = 240 MHz	Switch OFF		1.4	2	pF
C <sub>OFF(USB)</sub>	USB path OFF capacitance	$V_{CC} = 3.3 \text{ V}, V_{I/O} = 0 \text{ or } 3.3 \text{ V}$ f = 240 MHz	Switch OFF		1.6	2	pF
C <sub>I</sub>	Digital input capacitance	$V_{CC} = 3.3 \text{ V}, V_{I} = 0 \text{ or } 2 \text{ V}$			2.2		рF
O <sub>ISO</sub>	OFF Isolation	$V_{CC}$ = 2.3 V to 4.8 V, $R_L$ = 50 $\Omega$ , f = 240 MHz	Switch OFF		-34		dB
X <sub>TALK</sub>	Crosstalk	$V_{CC}$ = 2.3 V to 4.8 V, $R_L$ = 50 $\Omega$ , f = 240 MHz	Switch ON		-37		dB
B <sub>W(MHL)</sub>	MHL path -3-dB bandwidth	$V_{CC}$ = 2.3 V to 4.8 V, $R_L$ = 50 $\Omega$ , f = 240 MHz	Switch ON		6.1		GHz
B <sub>W(USB)</sub>	USB path -3-dB bandwidth	$V_{CC}$ = 2.3 V to 4.8 V, $R_L$ = 50 $\Omega$ ,	Switch ON		6.1		GHz
SUPPLY						•	
V <sub>CC</sub>	Power supply voltage			2.3		4.8	V
I <sub>CC</sub>	Positive supply current	$V_{CC}$ = 4.8 V, $V_{IN}$ = $V_{CC}$ or GND, $V_{I/O}$ = 0 V, Switch ON or OFF			30	50	μΑ
I <sub>cc, HZ</sub>	Power supply current in high-Z mode	$V_{CC}$ = 4.8 V, $V_{IN}$ = $V_{CC}$ or GND, V Switch ON or OFF, $\overline{OE}$ = H		5	10	μΑ	

# 6.7 Timing Requirements

				MIN	NOM	MAX	UNIT
t <sub>pd</sub>	Propagation delay				100		ps
t <sub>switch</sub>	Switching time (SEL to output)	See Figure 1				600	ns
t <sub>ZH, ZL</sub> (MHL)	MHL enable time (OE to output)	V <sub>I/O</sub> = 3.3 V or 0 V			100		μs
t <sub>HZ, LZ</sub> (MHL)	MHL disable time ( $\overline{\text{OE}}$ to output)	V <sub>I/O</sub> = 3.3 V OI U V	$R_L = 50 \Omega,$ $C_L = 5 pF,$		200		ns
t <sub>ZH, ZL</sub> (USB)	USB enable time (OE to output)	V <sub>I/O</sub> = 0.8 V or 0 V	V <sub>CC</sub> = 2.3 V to 4.8 V		100		μs
t <sub>HZ, LZ</sub> (USB)	USB disable time (OE to output)	V <sub>I/O</sub> = 0.0 V 01 0 V			200		ns
t <sub>SK(P)</sub>	Skew of opposite transitions of sam	e output			20		ps



- (1) All input pulses are suppleid by generators having the following characteristics: PRR  $\leq$  10 MHz,  $Z_O$  = 50  $\Omega$  ,  $t_r$  < 5 ns,  $t_f$  < 5 ns
- (2)  $C_{\text{\scriptsize L}}$  includes probe and jig capacitance.

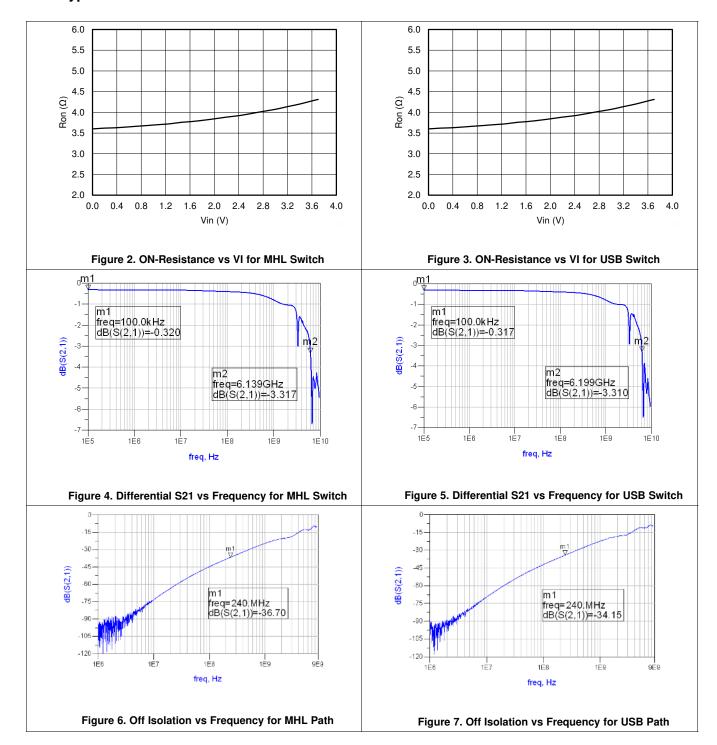
Figure 1. Timing Diagram

Submit Documentation Feedback

Copyright © 2012–2017, Texas Instruments Incorporated

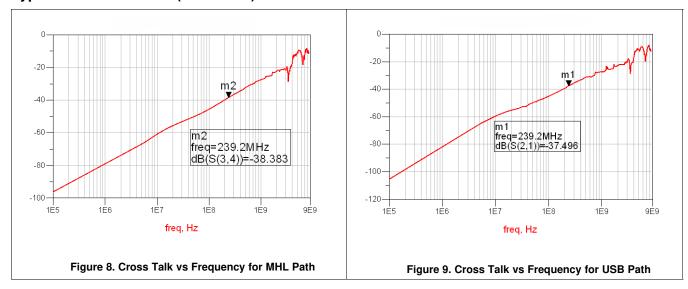


# 6.8 Typical Characteristics



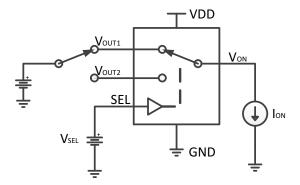


# **Typical Characteristics (continued)**





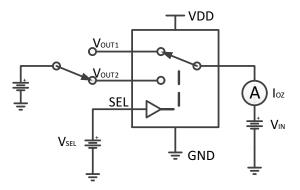
# 7 Parameter Measurement Information



# Channel ON

Ron = (Von - VI/01) / Ion or (Von - VI/02) / Ion VSEL = H or L

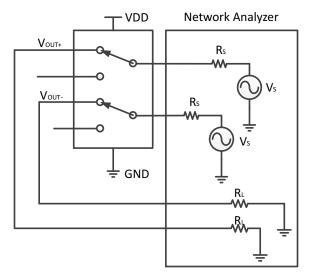
Figure 10. ON-State Resistance (R<sub>ON</sub>)



Channel OFF

VSEL = H or L

Figure 11. OFF Leakage Current (I<sub>OZ</sub>)



Channel ON

Vsel = H or L Rs=RL= $50\Omega$ 

Figure 12. Bandwidth (BW)



# 8 Detailed Description

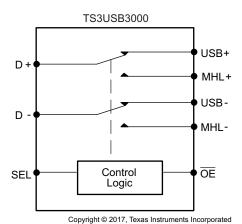
#### 8.1 Overview

The TS3USB3000 device is a 2-channel SPDT switch specially designed for the switching of high-speed MHL and USB 2.0 and 3.0 signals in handset and consumer applications, such as cell phones, digital cameras, and notebooks with hubs or controllers with limited USB I/Os. The wide bandwidth (6.1 GHz) of this switch allows signals to pass with minimum edge and phase distortion. The device multiplexes differential outputs from a USB host device to one of two corresponding outputs or from one USB connector to two processors or controllers. The switch is bidirectional and offers little or no attenuation of the high-speed signals at the outputs. The device also has a low power mode that reduces the power consumption to 5  $\mu$ A for portable applications with a battery or limited power budget.

The device is designed for low bit-to-bit skew and high channel-to-channel noise isolation, and is compatible with various standards, such as high-speed USB 2.0 (480 Mbps).

The TS3USB3000 device integrates ESD protection cells on all pins, is available in a tiny UQFN package (1.5 mm × 2 mm) and is characterized over the free-air temperature range from -40°C to +85°C.

#### 8.2 Functional Block Diagram



# 8.3 Feature Description

#### 8.3.1 Low Power Mode

The TS3USB3000 has a low power mode that reduces the power consumption to 5  $\mu$ A while the device is not in use. To put the device in low power mode and disable the switch, the bus-switch enable pin  $\overline{OE}$  must be supplied with a logic High signal.

#### 8.3.2 Overvoltage Protection when 9-V Short to D- Pin

This section describes how to protect the TS3USB3000 and the surrounding system when the D- pin is exposed to voltages greater than 5 V and less than 9 V. Voltages higher than 9 V damages the device.

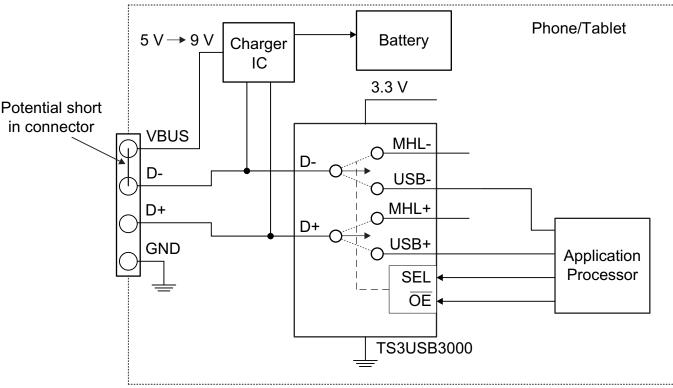
In charging applications it is possible for the USB plug to be inserted in such a way that the VBUS pin shorts to the D- pin of the connector. If there are peripherals on the D- pin that cannot tolerate conditions up to 9 V they can be damaged or destroyed. The TS3USB3000 can be used to protect the system from excess voltage if the correct precautions are taken.



#### **Feature Description (continued)**

In Figure 13, the system has an application processor (AP) that cannot survive 9 V on the USB data lines. The following procedure protects the system and the TS3USB3000. As stated in the *Absolute Maximum Ratings* table footnotes, the 9 V rating is only applicable while the VCC is powered within the voltage range of the recommended operating conditions and the  $\overline{\text{OE}}$  pin is high.

- 1. After a charger is connected to the USB port, the AP detects that a DCP is attached.
- 2. The AP pulls the  $\overline{OE}$  pin high to disable the switches.
- 3. The AP communicates to the Charger that it can negotiate for a faster charging mode with VBUS at 9 V.
- 4. The TS3USB3000 is now in a low-power state with the switches disabled and can protect the AP.



Copyright © 2017, Texas Instruments Incorporated

Figure 13. Potential VBUS to D- Short Example



# **Feature Description (continued)**

#### 8.3.3 Pin Leakage

When the voltage on the D- pins rises above VCC +1 V a leakage path in the device starts conducting as shown in Figure 14. The amount of leakage depends on the VCC voltage and the pin voltage. This leakage is governed by Equation 1:

$$Pin Leakage = \frac{V_D - V_{CC}}{12000} \tag{1}$$

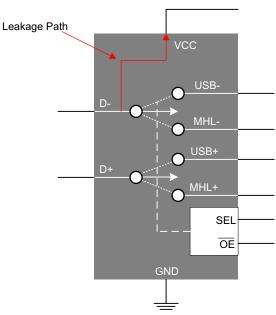


Figure 14. Potential Leakage Path D- to VCC

#### 8.4 Device Functional Modes

#### 8.4.1 High Impedance Mode

The TS3USB3000 has a high impedance mode that places all the signal paths in a Hi-Z state while the <u>device</u> is not in use. To put the device in high impedance mode and disable the switch, the bus-switch enable pin  $\overline{OE}$  must be supplied with a logic *High* signal as shown in Table 1.

**Table 1. Function Table** 

SEL	OE	SWITCH STATUS	
Χ	High	Both USB and MHL switches in High-Z	
Low	Low	D+/D- to USB+/USB-	
High	Low	D+/D- to MHL+/MHL-	



# 9 Application and Implementation

#### NOTE

Information in the following applications sections is not part of the TI component specification, and TI does not warrant its accuracy or completeness. TI's customers are responsible for determining suitability of components for their purposes. Customers should validate and test their design implementation to confirm system functionality.

## 9.1 Application Information

There are many USB applications in which the USB hubs or controllers have a limited number of USB I/Os or need to route signals from a single USB connector. The TS3USB3000 solution can effectively expand the limited USB I/Os by switching between multiple USB buses to interface them to a single USB hub or controller or route signals from on connector to two different locations.

# 9.2 Typical Application

Figure 15 represents a typical application of the TS3USB3000 USB/MHL switch. The TS3USB3000 is used to switch signals between the USB path, which goes to the baseband or application processor, or the MHL path, which goes to the HDMI to MHL bridge. The TS3USB3000 has internal 6-M $\Omega$  pulldown resistors on SEL and  $\overline{OE}$ . The pulldown on SEL ensure the USB channel is selected by default. The pulldown on  $\overline{OE}$  enables the switch when power is applied. The TS5A3157 is a separate SPDT switch that is used to switch between MHL's CBUS and the USB ID line that is needed for USB OTG (USB On-The-Go) application.

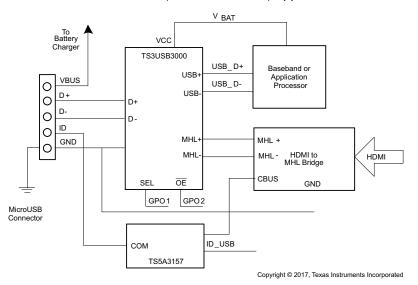


Figure 15. Typical TS3USB3000 Application

#### 9.2.1 Design Requirements

Design requirements of the MHL and USB 1.0,1.1, and 2.0 standards must be followed. The TS3USB3000 has internal 6-M $\Omega$  pulldown resistors on SEL and OE, so no external resistors are required on the logic pins. The internal pulldown resistor on SEL ensures the USB channel is selected by default. The internal pulldown resistor on  $\overline{\text{OE}}$  enables the switch when power is applied to VCC.

#### 9.2.2 Detailed Design Procedure

The TS3USB3000 can be properly operated without any external components. However, TI recommends that unused pins must be connected to ground through a  $50-\Omega$  resistor to prevent signal reflections back into the device.

Copyright © 2012–2017, Texas Instruments Incorporated



# **Typical Application (continued)**

# 9.2.3 Application Curves

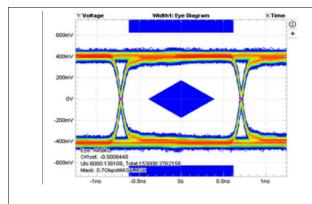


Figure 16. Eye Pattern: 0.7 Gbps With No Device

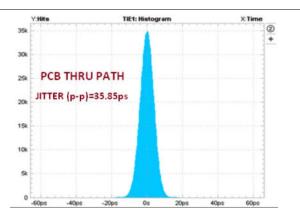
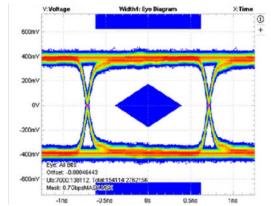
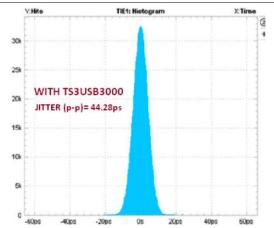


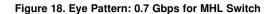
Figure 17. Time Interval Error Histogram: 0.7 Gbps With No Device



The TS3USB3000 contributes only 8.4 ps of peak-to-peak jitter for 0.7-Gbps data rate



The TS3USB3000 contributes only 8.4 ps of peak-to-peak jitter for 0.7-Gbps data rate



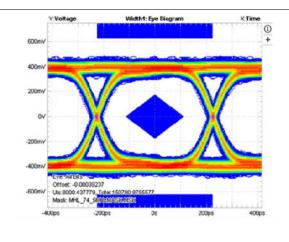


Figure 20. Eye Pattern: 2.2 Gbps With No Device



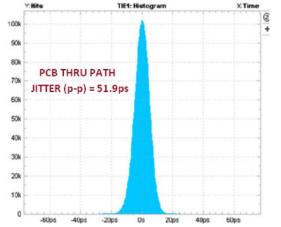
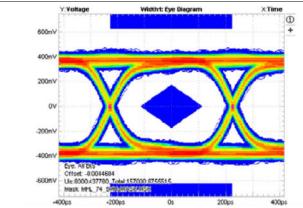


Figure 21. Time Interval Error Histogram: 2.2 Gbps With No Device

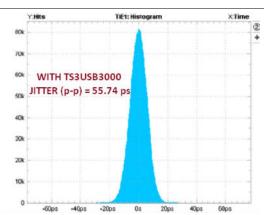


# **Typical Application (continued)**



The TS3USB3000 contributes only 3.8 ps of peak-to-peak jitter for 2.2-Gbps data rate

Figure 22. Eye Pattern: 2.2 Gbps for MHL Switch



The TS3USB3000 contributes only 3.8 ps of peak-to-peak jitter for 2.2-Gbps data rate

Figure 23. Time Interval Error Histogram: 2.2 Gbps for MHL Switch

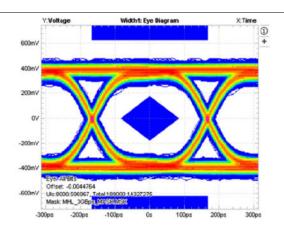


Figure 24. Eye Pattern: 3 Gbps With No Device

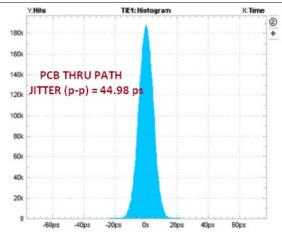
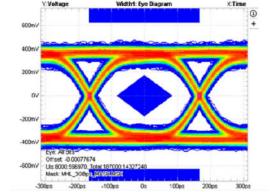
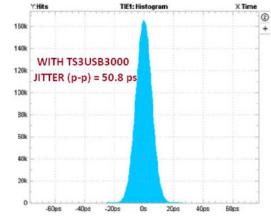


Figure 25. Time Interval Error Histogram: 3 Gbps With No Device



The TS3USB3000 contributes only 5.8 ps of peak-to-peak jitter for 3-Gbps data rate

Figure 26. Eye Pattern: 3 Gbps for MHL Switch



The TS3USB3000 contributes only 5.8 ps of peak-to-peak jitter for 3-Gbps data rate

Figure 27. Time Interval Error Histogram: 3 Gbps for MHL Switch

# TEXAS INSTRUMENTS

# **Typical Application (continued)**

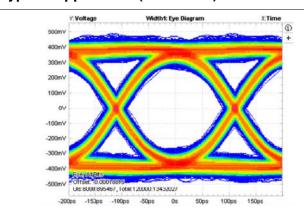


Figure 28. Eye Pattern: 4.5 Gbps With No Device

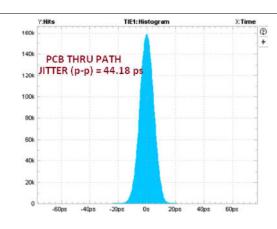
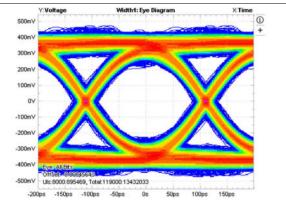
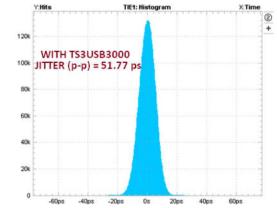


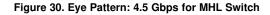
Figure 29. Time Interval Error Histogram: 4.5 Gbps With No Device



The TS3USB3000 contributes only 7.6 ps of peak-to-peak jitter for 4.5-Gbps data rate



The TS3USB3000 contributes only 7.6 ps of peak-to-peak jitter for 4.5-Gbps data rate



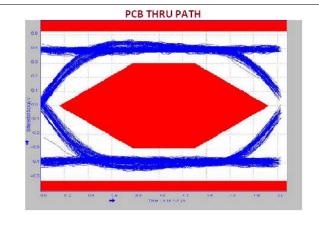
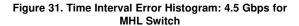


Figure 32. 480-Mbps USB 2.0 Eye Pattern With No Device



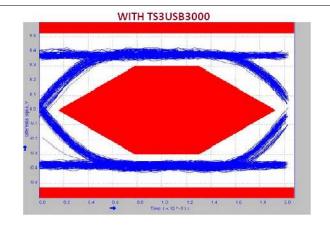


Figure 33. 480-Mbps USB 2.0 Eye Pattern for USB Switch



# 10 Power Supply Recommendations

Power to the device is supplied through the VCC pin and must follow the USB 1.0, 1.1, and 2.0 standards. TI recommends placing a bypass capacitor as close to the supply pin VCC as possible to help smooth out lower frequency noise to provide better load regulation across the frequency spectrum.

# 11 Layout

# 11.1 Layout Guidelines

Place supply bypass capacitors as close to VCC pin as possible and avoid placing the bypass caps near the D± traces.

The high-speed D± must match and be no more than 4 inches long; otherwise, the eye diagram performance may be degraded. A high-speed USB connection is made through a shielded, twisted pair cable with a differential characteristic impedance. In layout, the impedance of D+ and D- traces must match the cable characteristic differential impedance for optimal performance.

Route the high-speed USB signals using a minimum of vias and corners which reduces signal reflections and impedance changes. When a via must be used, increase the clearance size around it to minimize its capacitance. Each via introduces discontinuities in the signal's transmission line and increases the chance of picking up interference from the other layers of the board. Be careful when designing test points on twisted pair lines; through-hole pins are not recommended.

When it becomes necessary to turn 90°, use two 45° turns or an arc instead of making a single 90° turn. This reduces reflections on the signal traces by minimizing impedance discontinuities.

Do not route USB traces under or near crystals, oscillators, clock signal generators, switching regulators, mounting holes, magnetic devices or ICs that use or duplicate clock signals.

Avoid stubs on the high-speed USB signals because they cause signal reflections. If a stub is unavoidable, then the stub must be less than 200 mm.

Route all high-speed USB signal traces over continuous GND planes, with no interruptions.

Avoid crossing over anti-etch, commonly found with plane splits.

Due to high frequencies associated with the USB, a printed circuit board with at least four layers is recommended; two signal layers separated by a ground and power layer as shown in Figure 34.

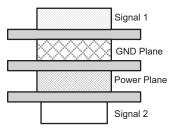


Figure 34. Four-Layer Board Stack-Up

The majority of signal traces must run on a single layer, preferably Signal 1. Immediately next to this layer must be the GND plane, which is solid with no cuts. Avoid running signal traces across a split in the ground or power plane. When running across split planes is unavoidable, sufficient decoupling must be used. Minimizing the number of signal vias reduces EMI by reducing inductance at high frequencies.



# 11.2 Layout Example

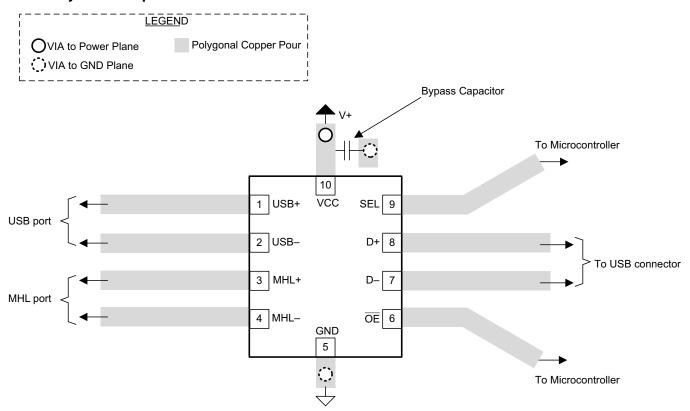


Figure 35. Package Layout Diagram



# 12 Device and Documentation Support

# 12.1 Documentation Support

#### 12.1.1 Related Documentation

For related documentation see the following:

- USB 2.0 Board Design and Layout Guidelines
- High-Speed Layout Guidelines Application Report
- High-Speed Interface Layout Guidelines

## 12.2 Receiving Notification of Documentation Updates

To receive notification of documentation updates, navigate to the device product folder on ti.com. In the upper right corner, click on *Alert me* to register and receive a weekly digest of any product information that has changed. For change details, review the revision history included in any revised document.

# 12.3 Community Resources

The following links connect to TI community resources. Linked contents are provided "AS IS" by the respective contributors. They do not constitute TI specifications and do not necessarily reflect TI's views; see TI's Terms of Lise

TI E2E™ Online Community TI's Engineer-to-Engineer (E2E) Community. Created to foster collaboration among engineers. At e2e.ti.com, you can ask questions, share knowledge, explore ideas and help solve problems with fellow engineers.

**Design Support** *TI's Design Support* Quickly find helpful E2E forums along with design support tools and contact information for technical support.

#### 12.4 Trademarks

E2E is a trademark of Texas Instruments.

All other trademarks are the property of their respective owners.

#### 12.5 Electrostatic Discharge Caution



These devices have limited built-in ESD protection. The leads should be shorted together or the device placed in conductive foam during storage or handling to prevent electrostatic damage to the MOS gates.

## 12.6 Glossary

SLYZ022 — TI Glossary.

This glossary lists and explains terms, acronyms, and definitions.

# 13 Mechanical, Packaging, and Orderable Information

The following pages include mechanical, packaging, and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser-based versions of this data sheet, refer to the left-hand navigation.

Copyright © 2012–2017, Texas Instruments Incorporated



# 13.1 Package Option Addendum

#### 13.1.1 Packaging Information

**Package Package Package** Lead/Ball Device Marking (5)(6) **Orderable Device** Status (1) Pins Eco Plan (2) MSL Peak Temp (4) Op Temp (°C) Finish (3) Type Drawing Qtv Green (RoHS TS3USB3000MRSER **ACTIVE UQFN RSE** 10 3000 **CU NIPDAU** Level-1-260C-UNLIM -40 to 85 DRJ. DR0. DRR & no Sb/Br) Green (RoHS TS3USB3000RSER ACTIVE UQFN RSF 10 3000 CU NIPDAU Level-1-260C-UNLIM -40 to 85 DSJ. DSO. DSR & no Sb/Br)

(1) The marketing status values are defined as follows:

**ACTIVE:** Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PRE\_PROD Unannounced device, not in production, not available for mass market, nor on the web, samples not available.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

**OBSOLETE:** TI has discontinued the production of the device.

(2) Eco Plan - The planned eco-friendly classification: Pb-Free (RoHS), Pb-Free (RoHS Exempt), or Green (RoHS & no Sb/Br) - please check http://www.ti.com/productcontent for the latest availability information and additional product content details.

**TBD:** The Pb-Free/Green conversion plan has not been defined.

**Pb-Free** (RoHS): TI's terms "Lead-Free" or "Pb-Free" mean semiconductor products that are compatible with the current RoHS requirements for all 6 substances, including the requirement that lead not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, TI Pb-Free products are suitable for use in specified lead-free processes.

**Pb-Free (RoHS Exempt):** This component has a RoHS exemption for either 1) lead-based flip-chip solder bumps used between the die and package, or 2) lead-based die adhesive used between the die and leadframe. The component is otherwise considered Pb-Free (RoHS compatible) as defined above.

Green (RoHS & no Sb/Br): TI defines "Green" to mean Pb-Free (RoHS compatible), and free of Bromine (Br) and Antimony (Sb) based flame retardants (Br or Sb do not exceed 0.1% by weight in homogeneous material)

- (3) Lead/Ball Finish Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead/Ball Finish values may wrap to two lines if the finish value exceeds the maximum column width.
- (4) MSL, Peak Temp. -- The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.
- (5) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device
- (6) Multiple Device markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.

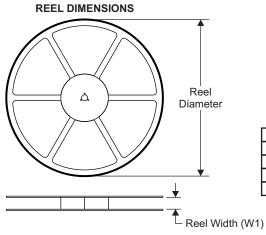
Important Information and Disclaimer: The information provided on this page represents TI's knowledge and belief as of the date that it is provided. TI bases its knowledge and belief on information provided by third parties, and makes no representation or warranty as to the accuracy of such information. Efforts are underway to better integrate information from third parties. TI has taken and continues to take reasonable steps to provide representative and accurate information but may not have conducted destructive testing or chemical analysis on incoming materials and chemicals. TI and TI suppliers consider certain information to be proprietary, and thus CAS numbers and other limited information may not be available for release.

In no event shall TI's liability arising out of such information exceed the total purchase price of the TI part(s) at issue in this document sold by TI to Customer on an annual basis.

Product Folder Links: TS3USB3000



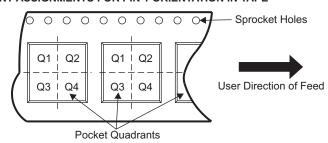
# 13.1.2 Tape and Reel Information



# TAPE DIMENSIONS KO P1 BO BO Cavity A0

Δ0	Discounting decisioned to accommodate the accommodate width
AU	Dimension designed to accommodate the component width
В0	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

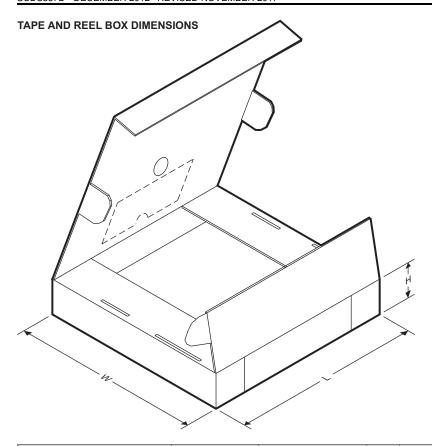
# QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



Device	Package Type	Package Drawing	Pins	SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
TS3USB3000MRSER	UQFN	RSE	10	3000	180.0	9.5	2.2	1.8	1.75	4.0	8.0	Q3
TS3USB3000RSER	UQFN	RSE	10	3000	180.0	9.5	2.2	1.8	1.75	4.0	8.0	Q3

Copyright © 2012–2017, Texas Instruments Incorporated





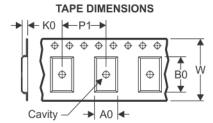
Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
TS3USB3000MRSER	UQFN	RSE	10	3000	189.0	185.0	36.0
TS3USB3000RSER	UQFN	RSE	10	3000	189.0	185.0	36.0

# **PACKAGE MATERIALS INFORMATION**

www.ti.com 13-Nov-2017

# TAPE AND REEL INFORMATION





	Dimension designed to accommodate the component width
B0	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

# QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



#### \*All dimensions are nominal

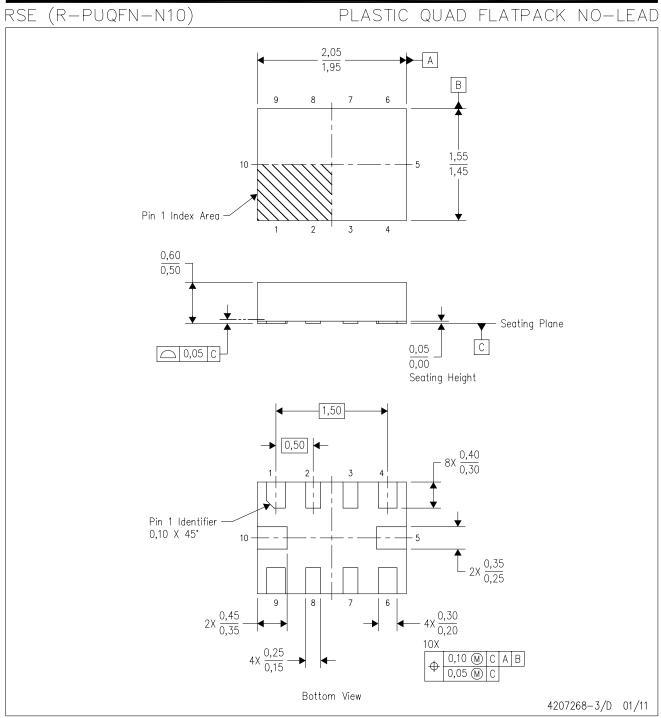
Device	Package Type	Package Drawing		SPQ	Reel Diameter	Reel Width	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
					(mm)	W1 (mm)						
TS3USB3000MRSER	UQFN	RSE	10	3000	180.0	9.5	2.2	1.8	0.75	4.0	8.0	Q3
TS3USB3000RSER	UQFN	RSE	10	3000	180.0	9.5	1.7	2.2	0.75	4.0	8.0	Q1

www.ti.com 13-Nov-2017



#### \*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
TS3USB3000MRSER	UQFN	RSE	10	3000	189.0	185.0	36.0
TS3USB3000RSER	UQFN	RSE	10	3000	189.0	185.0	36.0



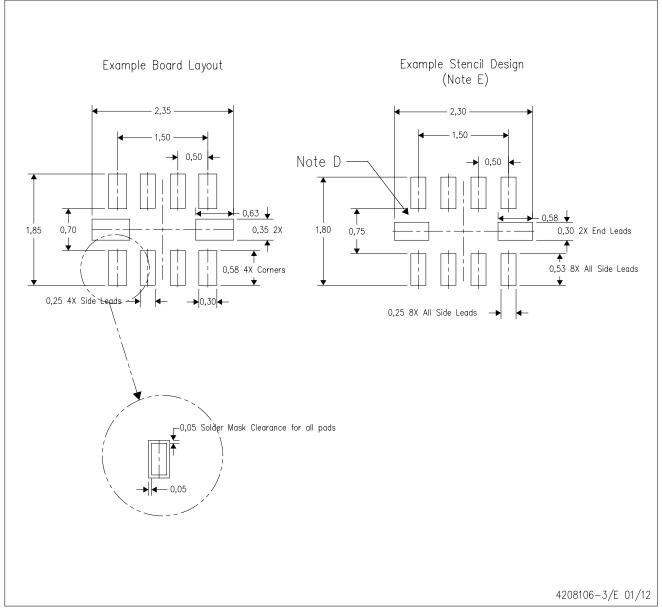
NOTES: All linear dimensions are in millimeters. Dimensioning and tolerancing per ASME Y14.5M-1994.

- B. This drawing is subject to change without notice.
  C. QFN (Quad Flatpack No-Lead) package configuration.
  D. This package complies to JEDEC MO-288 variation UEFD.



# RSE (R-PUQFN-N10)

# PLASTIC QUAD FLATPACK NO-LEAD



- NOTES: A. All linear dimensions are in millimeters.
  - B. This drawing is subject to change without notice.
  - C. Publication IPC-7351 is recommended for alternate designs.
  - D. Customers should contact their board fabrication site for minimum solder mask web tolerances between signal pads.
  - E. Maximum stencil thickness 0,127 mm (5 mils). All linear dimensions are in millimeters.
  - F. Laser cutting apertures with trapezoidal walls and also rounding corners will offer better paste release. Customers should contact their board assembly site for stencil design recommendations. Refer to IPC 7525 for stencil design considerations.
  - G. Side aperture dimensions over-print land for acceptable area ratio > 0.66. Customer may reduce side aperture dimensions if stencil manufacturing process allows for sufficient release at smaller opening.



#### IMPORTANT NOTICE

Texas Instruments Incorporated (TI) reserves the right to make corrections, enhancements, improvements and other changes to its semiconductor products and services per JESD46, latest issue, and to discontinue any product or service per JESD48, latest issue. Buyers should obtain the latest relevant information before placing orders and should verify that such information is current and complete.

TI's published terms of sale for semiconductor products (http://www.ti.com/sc/docs/stdterms.htm) apply to the sale of packaged integrated circuit products that TI has qualified and released to market. Additional terms may apply to the use or sale of other types of TI products and services.

Reproduction of significant portions of TI information in TI data sheets is permissible only if reproduction is without alteration and is accompanied by all associated warranties, conditions, limitations, and notices. TI is not responsible or liable for such reproduced documentation. Information of third parties may be subject to additional restrictions. Resale of TI products or services with statements different from or beyond the parameters stated by TI for that product or service voids all express and any implied warranties for the associated TI product or service and is an unfair and deceptive business practice. TI is not responsible or liable for any such statements.

Buyers and others who are developing systems that incorporate TI products (collectively, "Designers") understand and agree that Designers remain responsible for using their independent analysis, evaluation and judgment in designing their applications and that Designers have full and exclusive responsibility to assure the safety of Designers' applications and compliance of their applications (and of all TI products used in or for Designers' applications) with all applicable regulations, laws and other applicable requirements. Designer represents that, with respect to their applications, Designer has all the necessary expertise to create and implement safeguards that (1) anticipate dangerous consequences of failures, (2) monitor failures and their consequences, and (3) lessen the likelihood of failures that might cause harm and take appropriate actions. Designer agrees that prior to using or distributing any applications that include TI products, Designer will thoroughly test such applications and the functionality of such TI products as used in such applications.

TI's provision of technical, application or other design advice, quality characterization, reliability data or other services or information, including, but not limited to, reference designs and materials relating to evaluation modules, (collectively, "TI Resources") are intended to assist designers who are developing applications that incorporate TI products; by downloading, accessing or using TI Resources in any way, Designer (individually or, if Designer is acting on behalf of a company, Designer's company) agrees to use any particular TI Resource solely for this purpose and subject to the terms of this Notice.

TI's provision of TI Resources does not expand or otherwise alter TI's applicable published warranties or warranty disclaimers for TI products, and no additional obligations or liabilities arise from TI providing such TI Resources. TI reserves the right to make corrections, enhancements, improvements and other changes to its TI Resources. TI has not conducted any testing other than that specifically described in the published documentation for a particular TI Resource.

Designer is authorized to use, copy and modify any individual TI Resource only in connection with the development of applications that include the TI product(s) identified in such TI Resource. NO OTHER LICENSE, EXPRESS OR IMPLIED, BY ESTOPPEL OR OTHERWISE TO ANY OTHER TI INTELLECTUAL PROPERTY RIGHT, AND NO LICENSE TO ANY TECHNOLOGY OR INTELLECTUAL PROPERTY RIGHT OF TI OR ANY THIRD PARTY IS GRANTED HEREIN, including but not limited to any patent right, copyright, mask work right, or other intellectual property right relating to any combination, machine, or process in which TI products or services are used. Information regarding or referencing third-party products or services does not constitute a license to use such products or services, or a warranty or endorsement thereof. Use of TI Resources may require a license from a third party under the patents or other intellectual property of TI.

TI RESOURCES ARE PROVIDED "AS IS" AND WITH ALL FAULTS. TI DISCLAIMS ALL OTHER WARRANTIES OR REPRESENTATIONS, EXPRESS OR IMPLIED, REGARDING RESOURCES OR USE THEREOF, INCLUDING BUT NOT LIMITED TO ACCURACY OR COMPLETENESS, TITLE, ANY EPIDEMIC FAILURE WARRANTY AND ANY IMPLIED WARRANTIES OF MERCHANTABILITY, FITNESS FOR A PARTICULAR PURPOSE, AND NON-INFRINGEMENT OF ANY THIRD PARTY INTELLECTUAL PROPERTY RIGHTS. TI SHALL NOT BE LIABLE FOR AND SHALL NOT DEFEND OR INDEMNIFY DESIGNER AGAINST ANY CLAIM, INCLUDING BUT NOT LIMITED TO ANY INFRINGEMENT CLAIM THAT RELATES TO OR IS BASED ON ANY COMBINATION OF PRODUCTS EVEN IF DESCRIBED IN TI RESOURCES OR OTHERWISE. IN NO EVENT SHALL TI BE LIABLE FOR ANY ACTUAL, DIRECT, SPECIAL, COLLATERAL, INDIRECT, PUNITIVE, INCIDENTAL, CONSEQUENTIAL OR EXEMPLARY DAMAGES IN CONNECTION WITH OR ARISING OUT OF TI RESOURCES OR USE THEREOF, AND REGARDLESS OF WHETHER TI HAS BEEN ADVISED OF THE POSSIBILITY OF SUCH DAMAGES.

Unless TI has explicitly designated an individual product as meeting the requirements of a particular industry standard (e.g., ISO/TS 16949 and ISO 26262), TI is not responsible for any failure to meet such industry standard requirements.

Where TI specifically promotes products as facilitating functional safety or as compliant with industry functional safety standards, such products are intended to help enable customers to design and create their own applications that meet applicable functional safety standards and requirements. Using products in an application does not by itself establish any safety features in the application. Designers must ensure compliance with safety-related requirements and standards applicable to their applications. Designer may not use any TI products in life-critical medical equipment unless authorized officers of the parties have executed a special contract specifically governing such use. Life-critical medical equipment is medical equipment where failure of such equipment would cause serious bodily injury or death (e.g., life support, pacemakers, defibrillators, heart pumps, neurostimulators, and implantables). Such equipment includes, without limitation, all medical devices identified by the U.S. Food and Drug Administration as Class III devices and equivalent classifications outside the U.S.

TI may expressly designate certain products as completing a particular qualification (e.g., Q100, Military Grade, or Enhanced Product). Designers agree that it has the necessary expertise to select the product with the appropriate qualification designation for their applications and that proper product selection is at Designers' own risk. Designers are solely responsible for compliance with all legal and regulatory requirements in connection with such selection.

Designer will fully indemnify TI and its representatives against any damages, costs, losses, and/or liabilities arising out of Designer's non-compliance with the terms and provisions of this Notice.